AONR66820

80V N-Channel AlphaSGT2™

General Description

- Trench Power MOSFET - AlphaSGT2™ technology 80V
- Low $R_{DS(ON)}$
- Excellent Q_g x $R_{DS(ON)}$ Product (FOM)
- Pb-Free lead Plating, RoHS 2.0 and Halogen-Free Compliant
- Spike Optimized Process

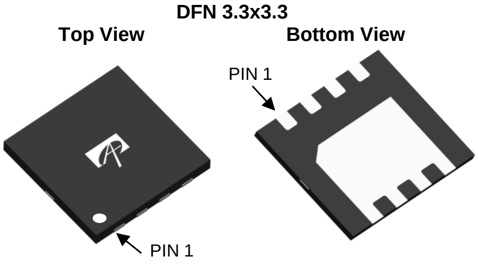
Applications

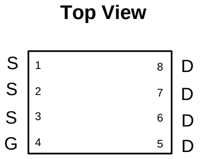
- Full Bridge MOSFET for isolated DC/DC converter
- DC/DC converters

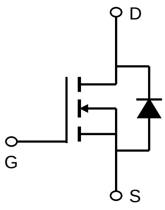
Product Summary

V_{DS}	80V
I_D (at V_{GS}=10V)	50A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 7.2mΩ
$R_{DS(ON)}$ (at V_{GS}=8V)	< 8.8mΩ

100% UIS Tested
100% Rg Tested







Orderable Part Number	Package Type	Form	Minimum Order Quantity
AONR66820	DFN 3.3x3.3	Tape & Reel	3000

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current[G]	T_C=25°C	I_D	50	A
	T_C=100°C		50	
Pulsed Drain Current[C]		I_{DM}	150	
Continuous Drain Current	T_A=25°C	I_{DSM}	17	A
	T_A=70°C		14	
Avalanche Current[C]		I_{AS}	35	A
Avalanche energy L=0.1mH[C]		E_{AS}	61	mJ
Power Dissipation[B]	T_C=25°C	P_D	104	W
	T_C=100°C		41	
Power Dissipation[A]	T_A=25°C	P_{DSM}	4.1	W
	T_A=70°C		2.6	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient[A]	t ≤ 10s	$R_{\theta JA}$	25	30	°C/W
Maximum Junction-to-Ambient[A D]	Steady-State		50	60	°C/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	1.0	1.2	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	80			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=80V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±20V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=$V_{GS,}$ I_D=250µA	2.9	3.5	4.1	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=17A		6	7.2	mΩ
		T_J=125°C		10.2	12.2	
		V_{GS}=8V, I_D=17A		7	8.8	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=17A		47		S
V_{SD}	Diode Forward Voltage	I_S=1A, V_{GS}=0V		0.72	1	V
I_S	Maximum Body-Diode Continuous Current [G]				50	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=40V, f=1MHz		1950		pF
C_{oss}	Output Capacitance			470		pF
C_{rss}	Reverse Transfer Capacitance			11		pF
R_g	Gate resistance	f=1MHz	0.3	0.6	0.9	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=40V, I_D=17A		25	50	nC
Q_{gs}	Gate Source Charge			9		nC
Q_{gd}	Gate Drain Charge			4.2		nC
Q_{oss}	Output Charge	V_{GS}=0V, V_{DS}=40V		36		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=50V, R_L=2.78Ω, R_{GEN}=3Ω		10		ns
t_r	Turn-On Rise Time			4		ns
$t_{D(off)}$	Turn-Off DelayTime			21		ns
t_f	Turn-Off Fall Time			4		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=17A, di/dt=500A/µs		28		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=17A, di/dt=500A/µs		140		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on R $_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Single pulse width limited by junction temperature $T_{J(MAX)}$=150° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.
G. The maximum current rating is package limited.
H. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

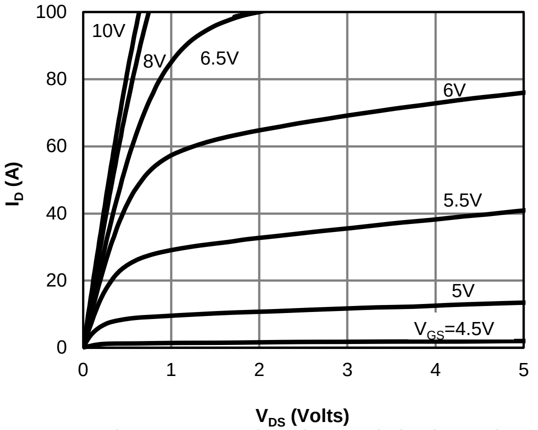


Figure 1: On-Region Characteristics (Note E)

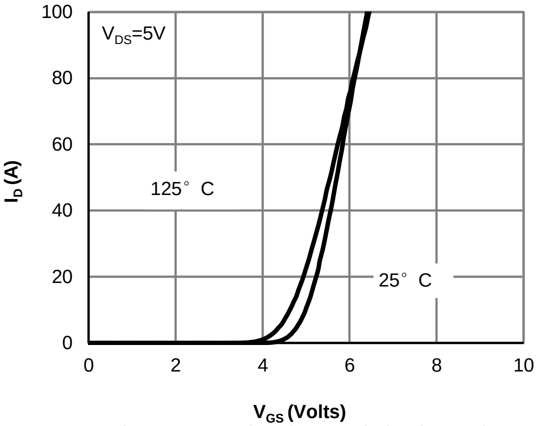


Figure 2: Transfer Characteristics (Note E)

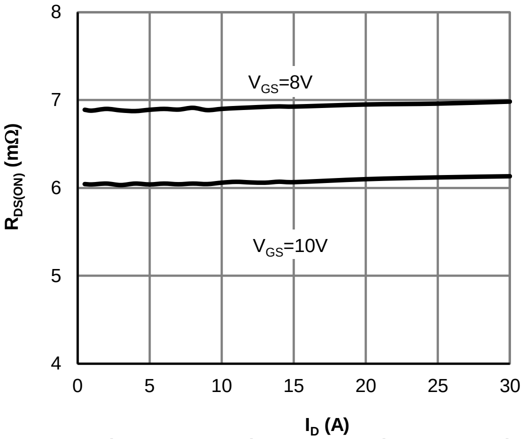


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

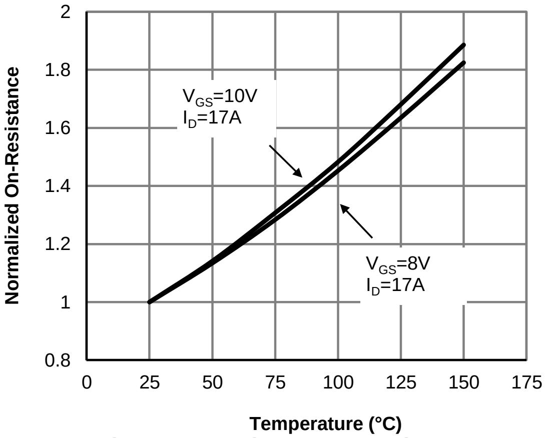


Figure 4: On-Resistance vs. Junction Temperature (Note E)

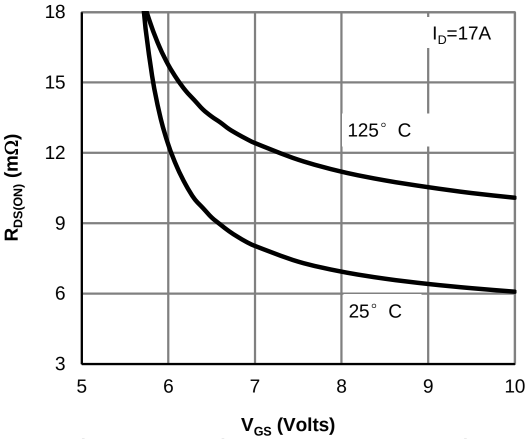


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

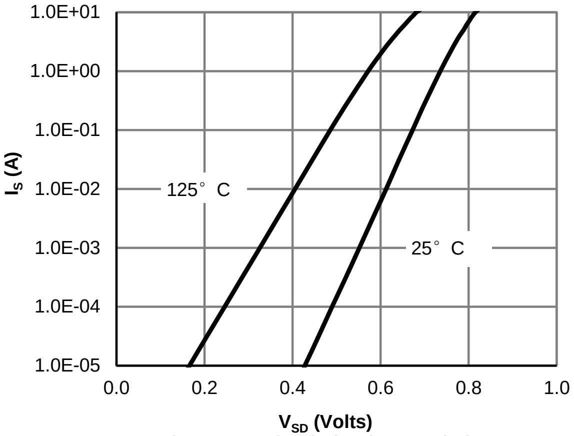


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

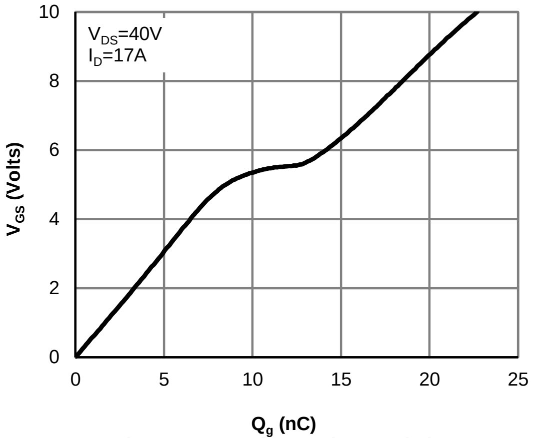


Figure 7: Gate-Charge Characteristics

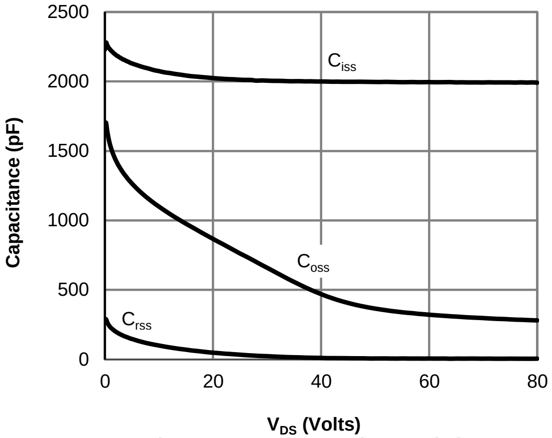


Figure 8: Capacitance Characteristics

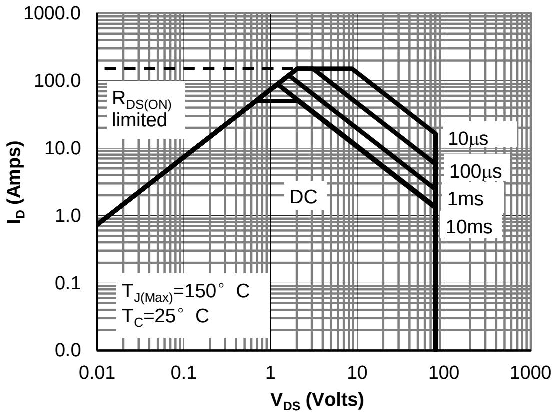


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

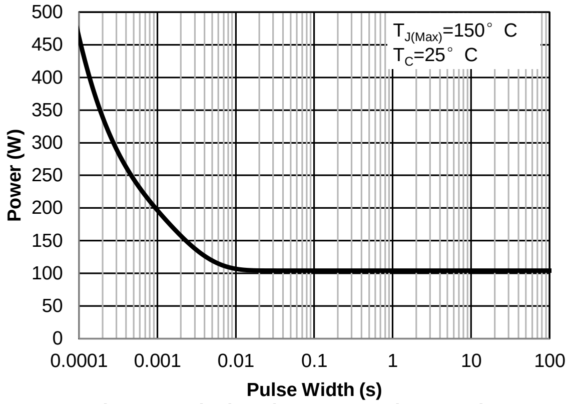


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

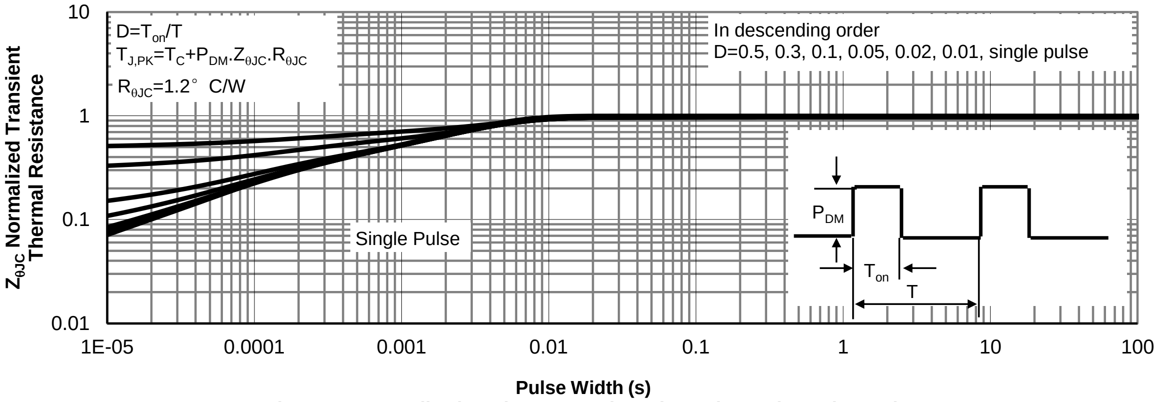


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

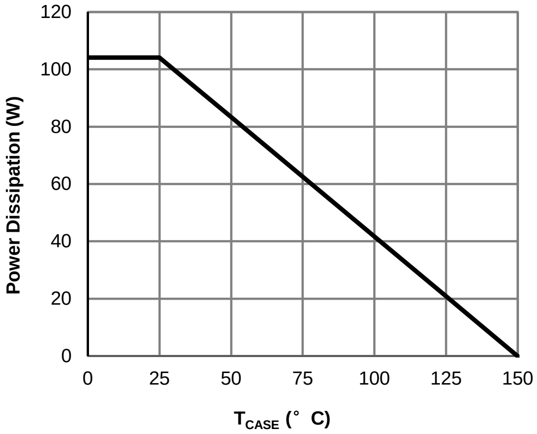


Figure 12: Power De-rating (Note F)

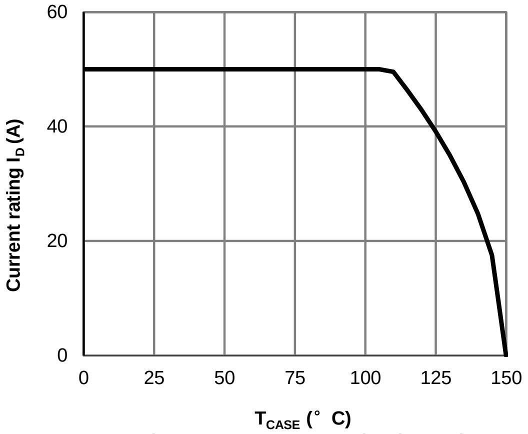


Figure 13: Current De-rating (Note F)

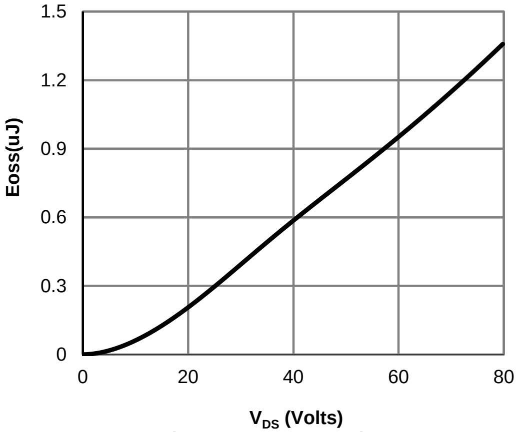


Figure 14: Coss stored Energy

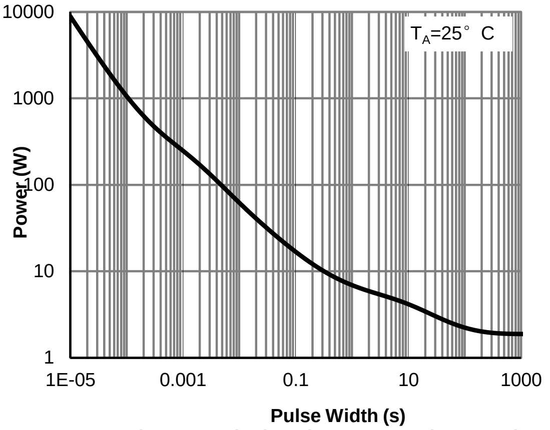


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

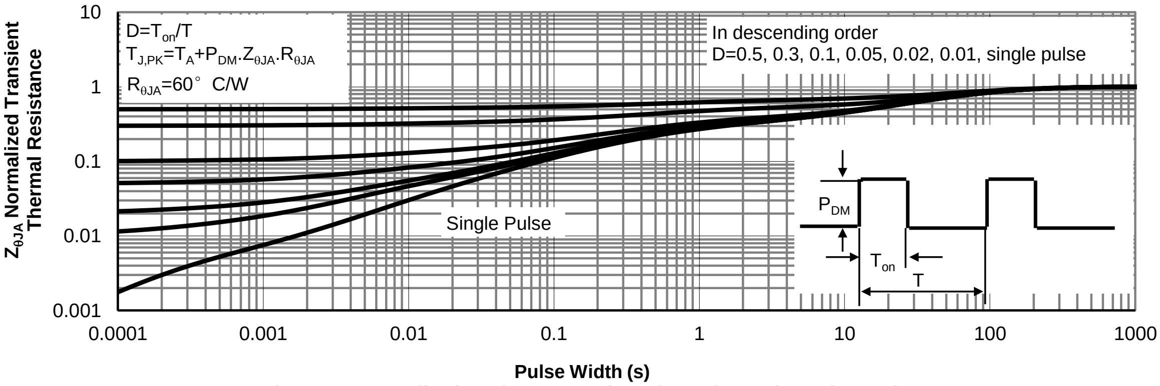


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

Figure A: Gate Charge Test Circuit & Waveforms

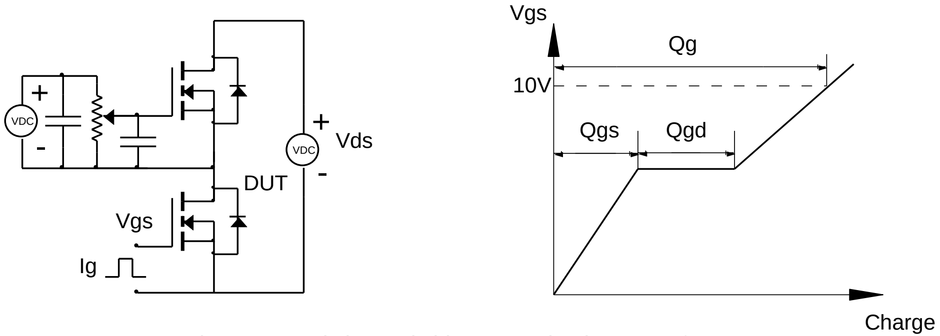


Figure B: Resistive Switching Test Circuit & Waveforms

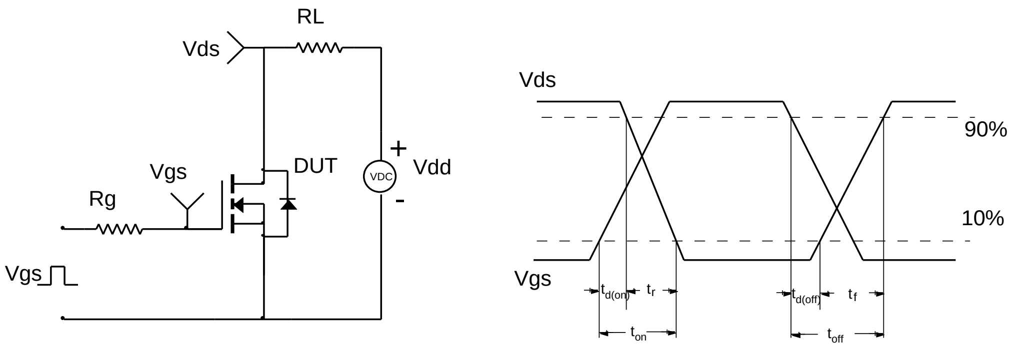


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

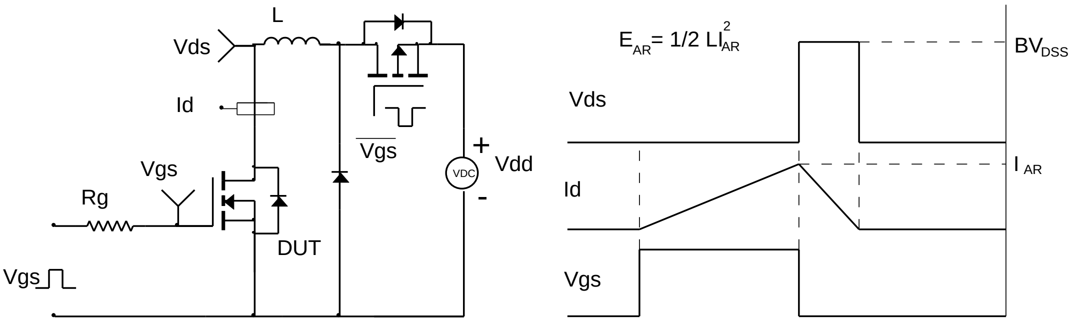


Figure D: Diode Recovery Test Circuit & Waveforms